



Bipolar NPN Bare Die – BTN6030

Part Description

The BTN6030 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 50V
- VCEO = 30V
- VEBO = 9V
- hFE = 360-760 @ VCE = 2V, IC = 0.5A
- VCE(Sat) = 1.1V @ IC = 1.5A, IB = 50mA
- fT = 150 MHz @ VCE = 6V, IE = 0A
- COBO = 50pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to RENESAS 2SD965 or ROHM 2SD2470

Die Size (Unawn)

840µm X 840µm, 33 Mils X 33 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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